



INFORMATION DISCLOSURE CITATION

PAGE 1 OF 2

Atty Docket No.
OPE-023Serial No.
10/627,043Applicant
Geoff Taylor et al.Filed
July 25, 2003Group
2828

US PATENT DOCUMENTS

Examiner Initials		Document No.	Date	Name	Class	Subclass	Filing date if approp.
W	A	3,919,656	11/11/75	Sokal et al.	330	51	
	B	4,424,525	1/3/84	Mimura	357	23	
	C	4,658,403	4/14/87	Takiguchi et al.	372	96	
	D	4,683,484	7/28/87	Derkits, Jr.	357	16	
	E	4,806,997	2/21/89	Simmons et al.	357	16	
	F	4,814,774	3/21/89	Herczfeld	342	372	
	G	4,827,320	5/2/89	Morkoc et al.	357	22	
	H	4,829,272	5/9/89	Kameya	333	139	
	I	4,899,200	2/6/90	Shur et al.	357	30	
	J	4,949,350	8/14/90	Jewell et al.	372	45	
	K	5,010,374	4/23/91	Cooke et al.	357	16	
	L	5,105,248	4/14/92	Burke et al.	357	24	
	M	5,202,896	4/13/93	Taylor	372	50	
	N	5,337,328	8/9/94	Lang et al.	372	45	
	O	5,386,128	1/31/95	Fossum et al.	257	183.1	
	P	5,422,501	6/6/95	Bayraktaroglu	257	195	
	Q	5,436,759	7/25/95	Dijaili et al.	359	333	
	R	5,698,900	12/16/97	Bozada et al.	257	744	
	S	6,031,243	2/29/00	Taylor	257	13	
	T	6,043,519	3/28/00	Shealy et al.	257	195	
	U	US2002 /0067877A1	6/6/02	Braun et al.			
	V						
	W						

EXAMINER

James Vannucci

DATE CONSIDERED

1-26-04



INFORMATION DISCLOSURE CITATION PAGE 2 OF 2		Atty Docket No. OPE-023	Serial No. 10/627,043
		Applicant Geoff Taylor et al.	
		Filed July 25, 2003	Group 2828
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)			
AA	<u>10-Gb/s High-Speed Monolithically Integrated Photoreceiver Using InGaAs p-i-n PD and Planar Doped InAlAs/InGaAs HEMT's</u> by Y. Akahori et al., IEEE Photonics Technology Letters, Vol. 4, No. 7, July 1992		
BB	<u>10-Gbit/s InP-Based High-Performance Monolithic Photoreceivers Consisting of p-i-n Photodiodes and HEMT's</u> by Kiyoto Takahata et al., IEICE TRANS. ELECTRON., Vol. E83-C, No. 6, June 2000		
CC	<u>10 Ghz Bandwidth Monolithic p-i-n Modulation-Doped Field Effect Transistor Photoreceiver</u> by N.K. Dutta et al., Appl. Phys. Lett., Vol. 63, No. 15, 11 October 1993		
DD	<u>20 Gbit/s Long Wavelength Monolithic Integrated Photoreceiver Grown on GaAs</u> by V. Hurm et al., Electronic Letters, Vol. 33, No. 7, 27 March 1997		
EE	<u>Heterojunction Field-Effect Transistor (HFET)</u> by G.W. Taylor et al., Electronics Letters, Vol. 22, No. 15, pp. 784-786, 17 July 1986		
FF	<u>High Temperature Annealing of Modulation Doped GaAs/AlGaAs Heterostructures for FET Applications</u> by H. Lee et al., 1983 IEEE/Cornell Conf. On High-Speed Semiconductor Devices & Ckts, 8/83		
GG	<u>Monolithic Integrated Optoelectronic Circuits</u> by M. Berroth et al., 0-7803-2442-0-8/95 IEEE, 1995		
HH	<u>Physical Layer Solution for Very Short Reach Applications Utilizing Parallel Optics</u> by Steve Ahart, Agilent Technologies, ONIDS 2002		
II	<u>Parallel Optics: the Solution for High-Speed Interconnects</u> downloaded from www.paralleloptics.org, December 2000, updated April, May, July, Sept., Nov 2001 and Jan, April and July 2002		
JJ	<u>Submicrometre Gate Length Scaling of Inversion Channel Heterojunction Field Effect Transistor</u> by P.A. Kiely et al., Electronics Letters, Vol. 30, No. 6, 17 March 1994		
KK	<u>Theoretical and Experimental Results for the Inversion Channel Heterostructure Field Effect Transistor</u> by G.W. Taylor et al., IEEE Proceedings-G, Vol 140, No. 6, December 1993		
LL	<u>Vertical-Cavity Surface-Emitting Laser Diodes with Post-Growth Wavelength Adjustment</u> by Wipiejewski et al., IEEE Photonics Technology Letters, Vol. 7, No. 7, July 1995		
MM	<u>Tunable VCSEL</u> by Chang-Hasnain, IEEE Journal on Selected Topics in Quantum Electronics, Vol. 6, No. 6 Nov/Dec 2000		
EXAMINER James Vannucci		DATE CONSIDERED 1-26-04	